LASER ANNEALING

ABSTRACT

A system for and method of processing an article such as a semiconductor wafer is disclosed. The wafer includes first and second surface which are segmented into a plurality of first and second zones. The first surface of the wafer, for example, on which devices or ICs are formed is processed by, for example, laser annealing while the second surface is heated with a backside heating source. Corresponding zones on the first and second surfaces are processed synchronously to reduce variations of post laser anneal thermal budge across the wafer.

Fig. 1